DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

BV_{DSS}	$R_{DS(on)}$ Max	I_D Max T_A = +25°C
60V	3Ω @ V_{GS} = 5V	0.3A

Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD Protected Up To 2kV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at https://www.diodes.com/products/automotive/automotive-products/.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/**
- **An Automotive-Compliant Part is Available Under Separate Datasheet (DMN601DWKQ)**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

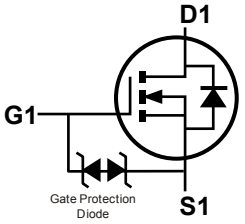
- Motor Control
- Power Management Functions

Mechanical Data

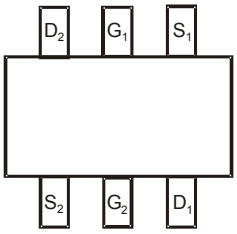
- Case: SOT363 (Standard)
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead-Free Plating). Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

SOT363 (Standard)

Top View



Equivalent Circuit



Top View
Internal Schematic

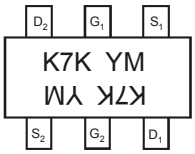
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN601DWK-7	SOT363 (Standard)	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

SOT363



K7K = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: I = 2021)
M or $\overline{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2005	……	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	S	……	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current (Note 5)	Continuous Pulsed (Note 6)	I_D	305 800	mA

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 10μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	μA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.6	2.5	V	V_{DS} = 10V, I_D = 1mA
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	1.3 1.5	2.0 3.0	Ω	V_{GS} = 10V, I_D = 0.5A V_{GS} = 5V, I_D = 0.05A
Forward Transfer Admittance	$\|Y_{fs}\|$	80	—	—	ms	V_{DS} =10V, I_D = 0.2A
Diode Forward Voltage	V_{SD}	0.5	0.8	1.4	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	30	50	pF	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	4.2	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.9	5.0	pF	
Gate Resistance	R_g	—	133	—	Ω	f = 1MHz , V_{GS} = 0V, V_{DS} = 0V
Total Gate Charge	Q_g	—	304	—	pC	V_{GS} = 4.5V, V_{DS} = 10V, I_D = 250mA
Gate-Source Charge	Q_{gs}	—	203	—	pC	
Gate-Drain Charge	Q_{gd}	—	84	—	pC	
Turn-On Delay Time	$t_{D(on)}$	—	3.9	—	nS	V_{DD} = 30V, V_{GS} = 10V, R_G = 25Ω, I_D = 200mA
Turn-On Rise Time	t_r	—	3.4	—	nS	
Turn-Off Delay Time	$t_{D(off)}$	—	15.7	—	nS	
Turn-Off Fall Time	t_f	—	9.9	—	nS	

Notes: 5. Device mounted on FR-4 PCB.
6. Pulse width ≤10μS, duty cycle ≤1%.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

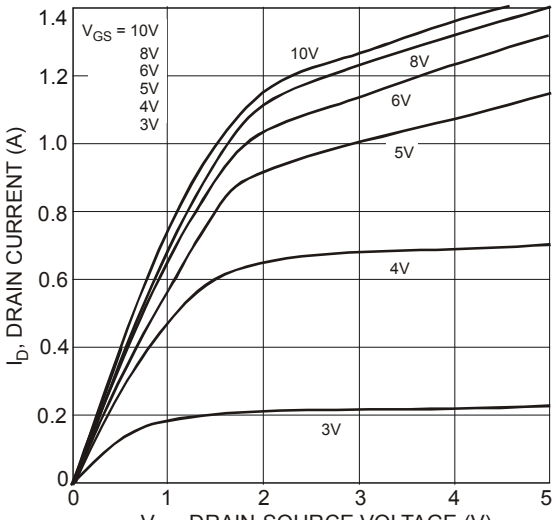


Figure 1 Typical Output Characteristics

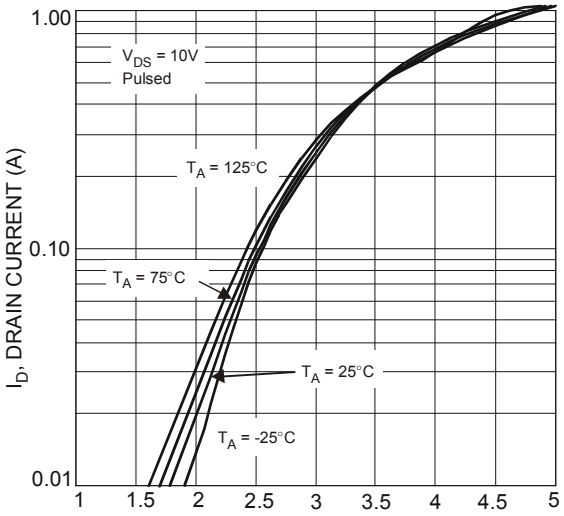


Figure 2 Typical Transfer Characteristics

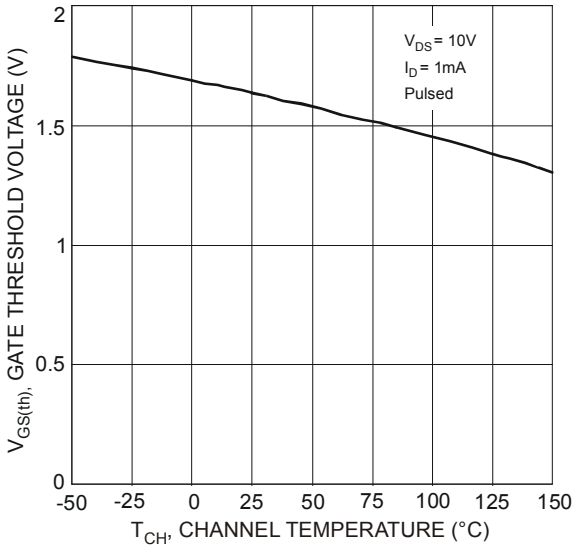


Figure 3 Gate Threshold Voltage vs. Channel Temperature

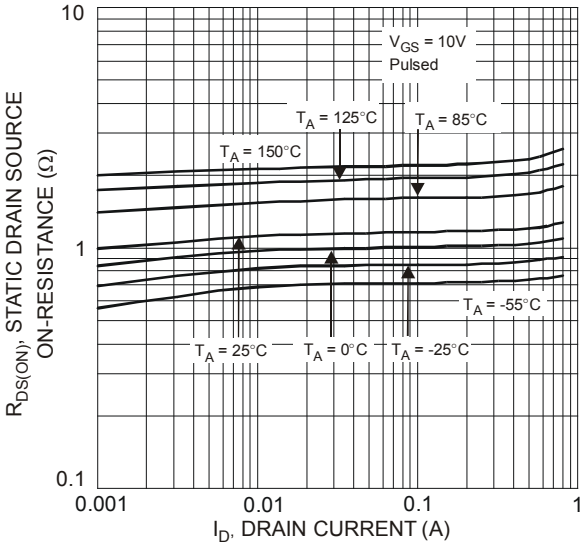


Figure 4 Static Drain-Source On-Resistance vs. Drain Current

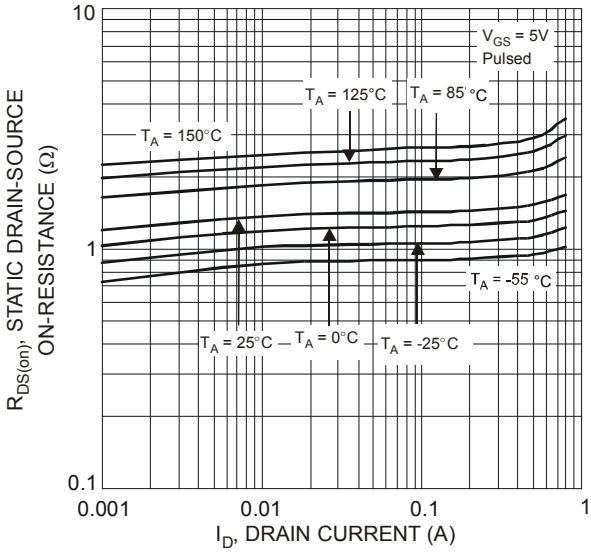


Figure 5 Static Drain-Source On-Resistance vs. Drain Current

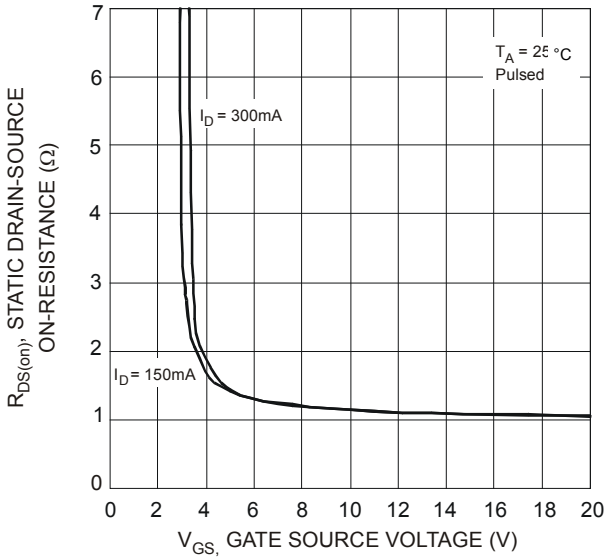


Figure 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

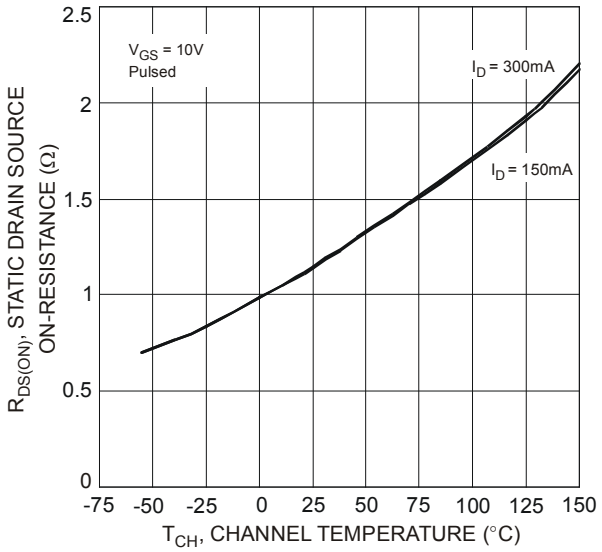


Figure 7 Static Drain-Source On-State Resistance vs. Channel Temperature

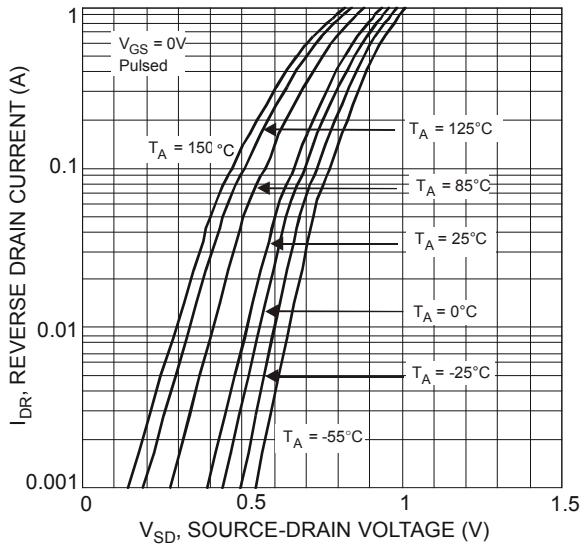


Figure 8 Reverse Drain Current vs. Source-Drain Voltage

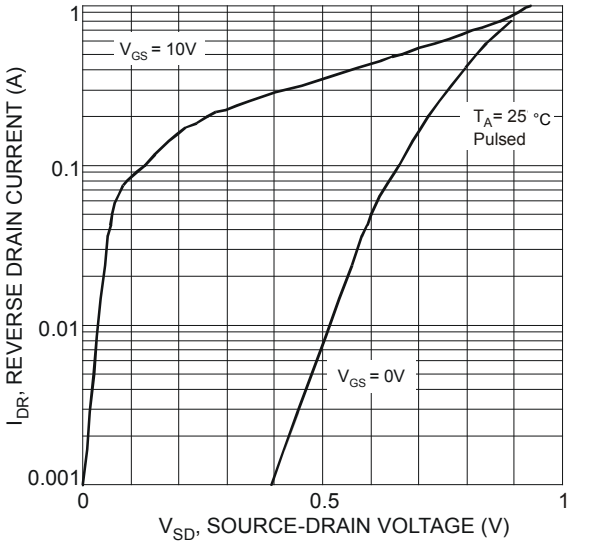


Figure 9 Reverse Drain Current vs. Source-Drain Voltage

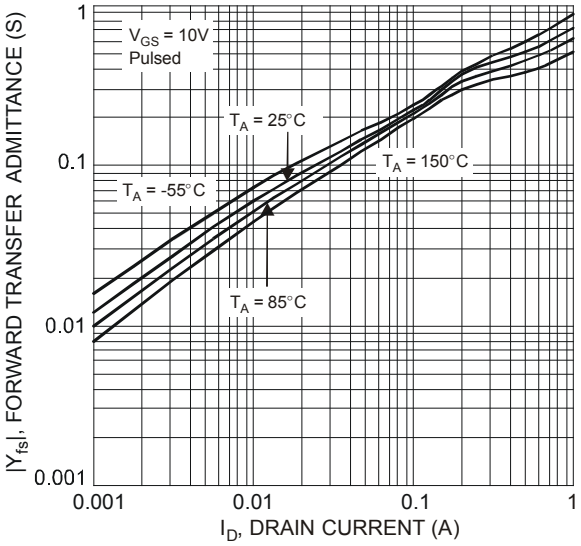


Figure 10 Forward Transfer Admittance vs. Drain Current

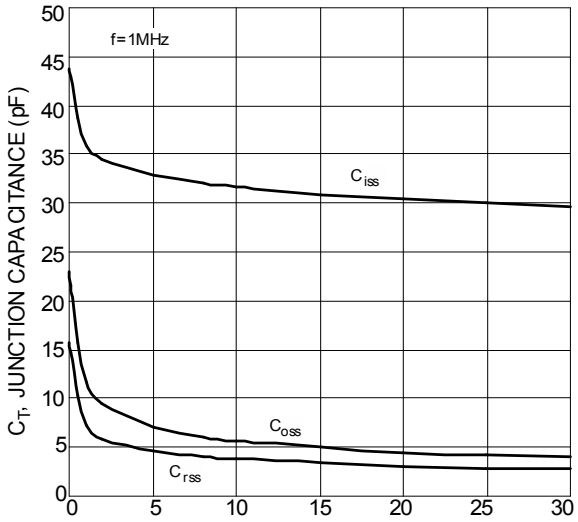


Figure 11 Typical Junction Capacitance

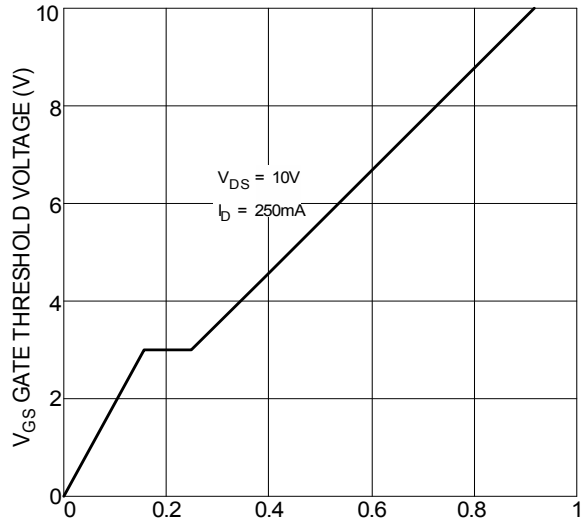


Figure 12 Gate Charge

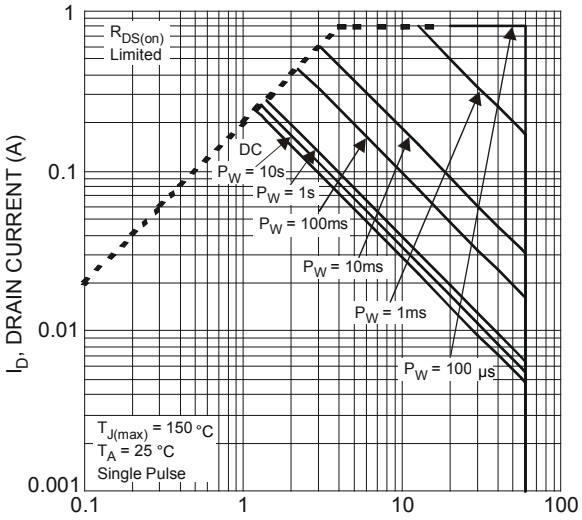


Figure 13 SOA, Safe Operation Area

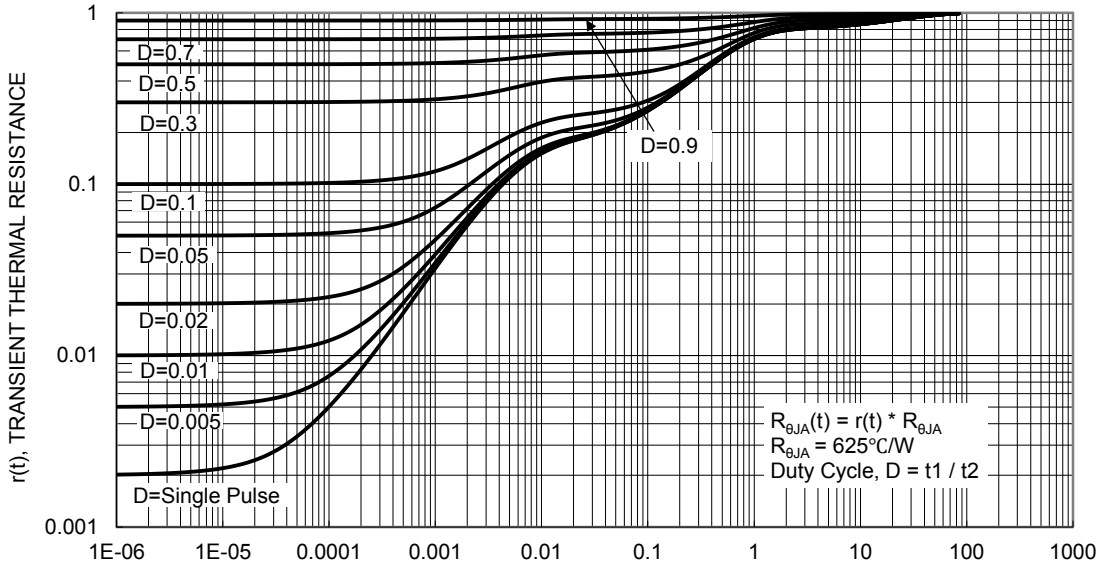
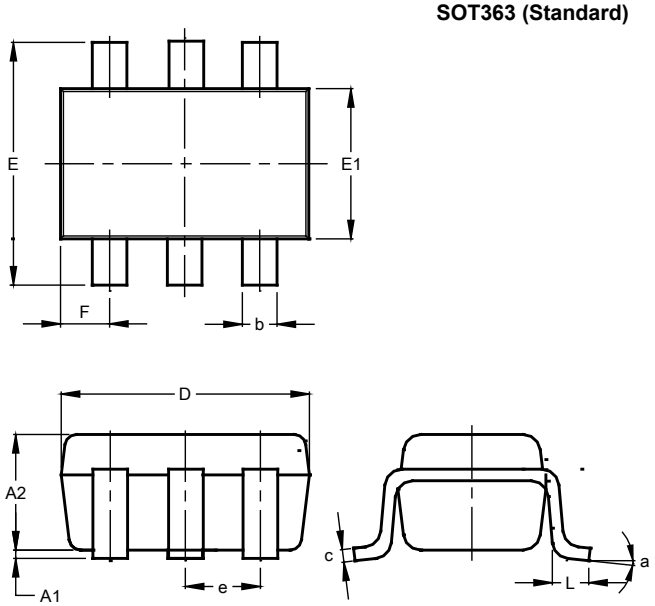


Figure 14 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363 (Standard)

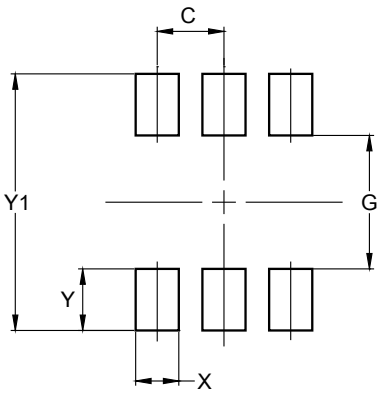


SOT363 (Standard)			
Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.10	0.35	0.225
c	0.08	0.22	0.15
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
F	0.25	0.45	0.35
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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